

Substitute for forms 1449A/PTO & 1449B/PTO	ATTORNEY'S DKT NO. 009683-485	APPLICATION NO. Unassigned 101694,780
	APPLICANT Tsukasa OOISHI	
	FILING DATE October 28, 2003	GROUP <del>Unassigned</del> 2818
	FIRST INFORMATION DISCLOSURE STATEMENT BY APPLICANT	

U.S. PATENT DOCUMENTS				
Examiner Initials	Document Number	Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Issue/Publication Date (MM-DD-YYYY)
<i>W</i>	6,347,056		Ledford et al.	02-12-2002
<i>W</i>	6,201,754		Ooishi et al.	03-13-2001
<i>W</i>	6,337,828		Ooish et al.	01-08-2002
<i>W</i>	6,256,224		Perner et al.	07-03-2001
<i>W</i>	2003/0081453		Hidaka	05-01-2003

FOREIGN PATENT DOCUMENTS					
Examiner Initials	Document Number	Kind Code (if known)	Country	Date of Publication (MM-DD-YYYY)	Translation Yes No
<i>W</i>	11-339470		Japan	12-10-1999	X

NON-PATENT LITERATURE DOCUMENTS	
Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>W</i>	Roy SCHEUERLEIN et al., "A 10ns Read and Write Non-Volatile Memory Array using a Magnetic Tunnel Junction and FET Switch in Each Cell," IEEE ISSCC Digest of Technical Papers, February 2000, pp. 94-95, 128-129, 409-410.
<i>W</i>	NIKKEI MICRODEVICES, "Forefront of Non-Volatile Memory The Future in Intel's Mind: From Flash Memory to "OUM", March 2002, pp. 65-78 (with partial English Translation).

Examiner Signature <i>Leo duong</i>	Date Considered 11/07
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.